

I GBT

Insulated Gate Bipolar Transistor

I GBT MOSFET GTR

I GBT

5kHz 40kHz 40kHz 150kHz

I GBT

I GBT

I GBT

I GBT

1

I GBT

I GBT

2

I GBT

Vces

Vces

I GBT

FRED

I GBT Vce(sat)

+VG=14 15V -VG=5 10V

Rg I GBT

Rg

Rg

()

Rg

5

100

20K 30K

I GBT

I GBT

, 表面平整度 35um 同时表面粗糙度小于15um

1/3

IGBT

1/3

IGBT